

What is claimed is:

1. A light emitting element, comprising a light emitting  
element layer between a first electrode and a second electrode,  
5 wherein

one of the first electrode and the second electrode is  
disposed as a light-emitting-side electrode on a side from which  
light is emitted to outside,

another one of the first electrode and the second electrode,  
10 which is formed as a back-side electrode positioned on a back side  
of the light-emitting-side electrode, is formed as a  
semitransparent electrode for partially transmitting incident  
light from a side of the light emitting element layer, and

an antireflective layer is provided on a back side of the  
15 semitransparent electrode.

2. A light emitting element according to claim 1, wherein a  
metal layer with a thickness reduced to a level of a thin film  
through which light can be transmitted or a metal layer with a  
20 mesh pattern provided with apertures for transmitting light is  
used in the semitransparent electrode.

3. A light emitting element according to claim 1, wherein an  
Ag layer or an MgAg layer with a thickness of 20 nm or less is  
25 used in the semitransparent electrode.

4. A light emitting element according to claim 1, wherein molybdenum or a chromium oxide is used in the antireflective layer.

5. A light emitting display, comprising a light emitting  
5 element with a light emitting element layer provided between a first electrode and a second electrode, wherein

the first electrode is formed over a transparent substrate disposed on a side from which light is emitted to outside of the display and is an electrode capable of transmitting light emitted  
10 from the light emitting element layer,

the second electrode is formed on a back side of the first electrode so as to be opposed to the first electrode with the light emitting element layer interposed therebetween and is a semitransparent electrode for partially transmitting incident  
15 light from a side of the light emitting element layer, and

an antireflective layer is provided on a back side of the second electrode.

6. A light emitting display according to claim 5, wherein a  
20 metal layer with a thickness reduced to a level of a thin film through which light can be transmitted or a metal layer with a mesh pattern provided with apertures for transmitting light is used in the semitransparent electrode.

25 7. A light emitting display according to claim 5, wherein an Ag layer or an MgAg layer with a thickness of 20 nm or less is

used in the semitransparent electrode.

8. A light emitting display according to claim 5, wherein molybdenum or a chromium oxide is used in the antireflective layer.

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9. A light emitting display according to claim 5, the display further comprising a plurality of pixels, each pixel comprising the light emitting element and a thin-film transistor for controlling light emission from the light emitting element, wherein

10 the thin-film transistor is formed closer to the substrate than the light emitting element, and

an antireflective light-blocking layer for blocking entry of ambient light and for preventing reflection of ambient light is provided between at least a region where an active layer of  
15 the thin-film transistor is formed and the substrate.

10. A display, comprising an electroluminescence element with a light emitting element layer provided between an anode and a cathode, wherein

20 the anode is formed over a transparent substrate disposed on a side from which light is emitted to outside and comprises an electrode capable of transmitting light emitted from the light emitting element layer,

the cathode is formed on a back side of the anode so as  
25 to be opposed to the anode with the light emitting element layer interposed therebetween and comprises a semitransparent electrode

capable of partially transmitting incident light from a side of the light emitting element layer, and

an antireflective layer is formed on a back side of the cathode.

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11. A display according to claim 10, wherein a metal layer with a thickness reduced to a level of a thin film through which light can be transmitted or a metal layer with a mesh pattern provided with apertures for transmitting light is used in the  
10 semitransparent electrode.

12. A display according to claim 10, wherein an Ag layer or an MgAg layer with a thickness of 20 nm or less is used in the semitransparent electrode.

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13. A display according to claim 10, wherein molybdenum or a chromium oxide is used in the antireflective layer.

14. A display according to claim 10, the display further  
20 comprising a plurality of pixels, each pixel comprising the electroluminescence element and a thin-film transistor for controlling light emission from the electroluminescence element, wherein

the thin-film transistor is formed closer to the substrate  
25 than the electroluminescence element, and

an antireflective light-blocking layer for blocking entry

of ambient light and for preventing reflection of ambient light is provided between at least a region where an active layer of the thin-film transistor is formed and the substrate.